



# 6th International Electronic Conference on Sensors and Applications

15 – 30 November 2019

Chairs

Dr. Stefano Mariani, Dr. Thomas B. Messervey,  
Dr. Alberto Vallan, Dr. Stefan Besse and  
Prof. Dr. Francisco Falcone

 POLITECNICO DI MILANO

Organized by:  *sensors* 

## Stochastic Mechanical Characterization of Polysilicon MEMS: a Deep Learning Approach

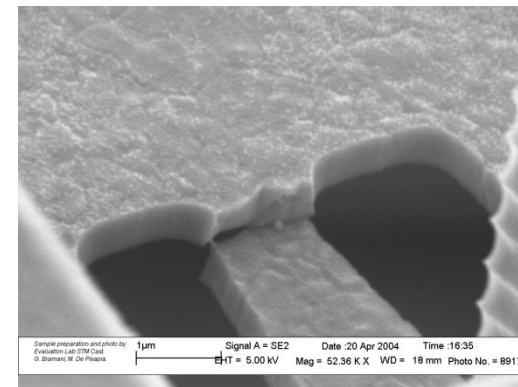
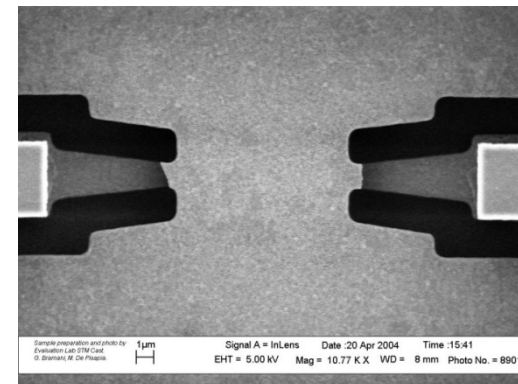
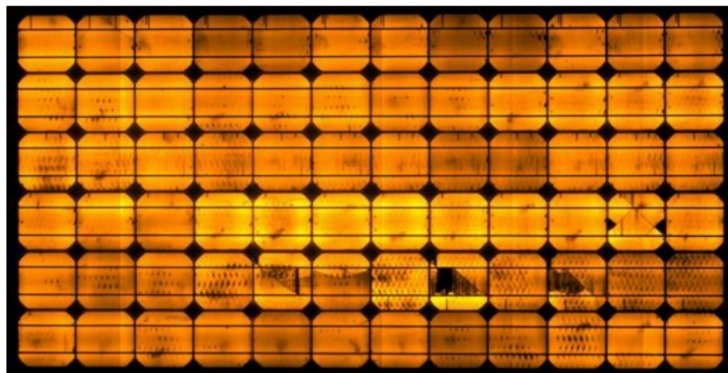
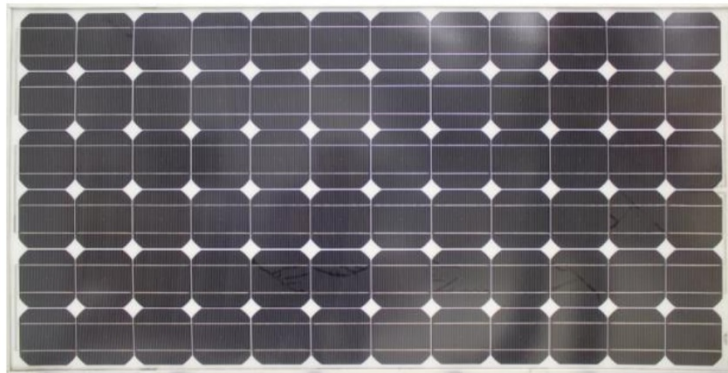


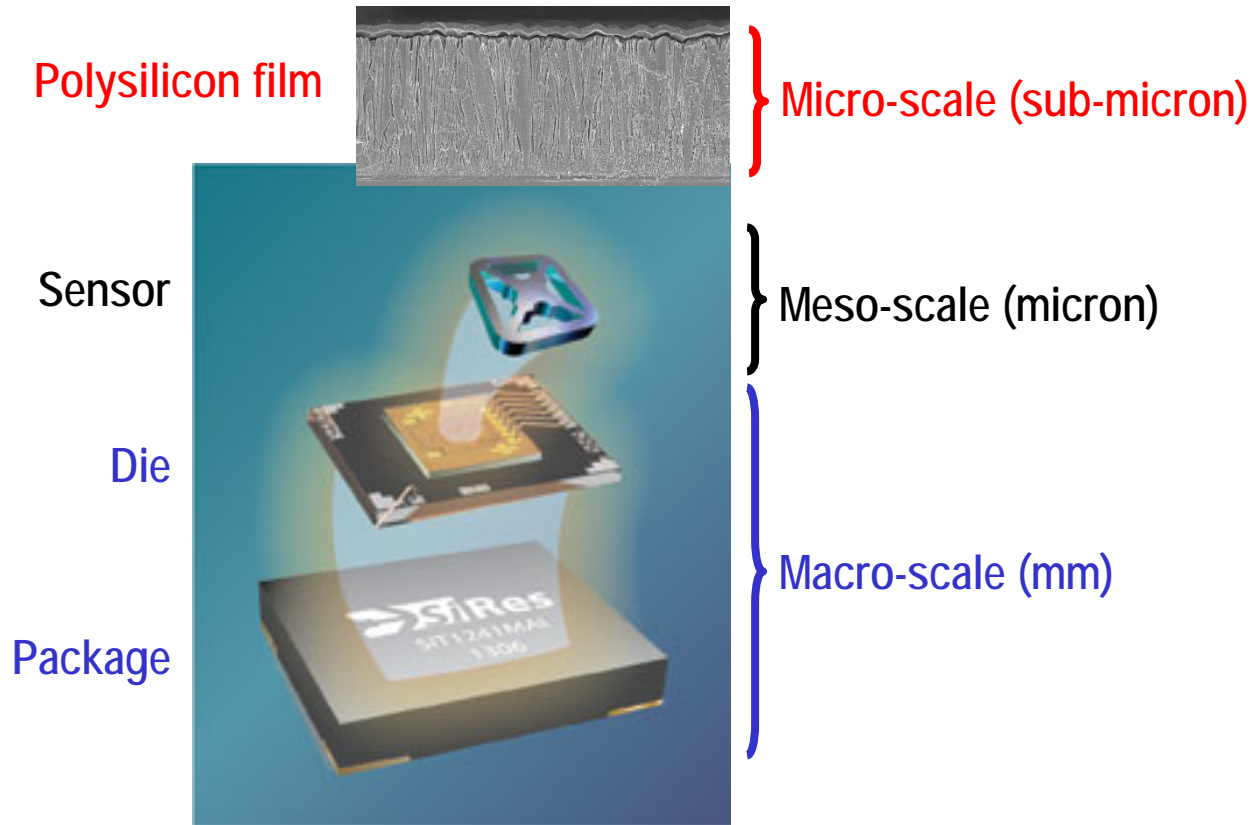
*José Pablo Quesada Molina, Luca Rosafalco and Stefano Mariani*

Politecnico di Milano, Department of Civil and Environmental Engineering  
and  
University of Costa Rica, Department of Mechanical Engineering

## failure of **POLYSILICON** (thin) films exposed to mechanical and thermal loads

Due to mechanical and thermal loads, (thin) Si films can break because of the propagation of inter- and/or trans-granular cracks

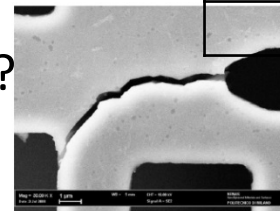


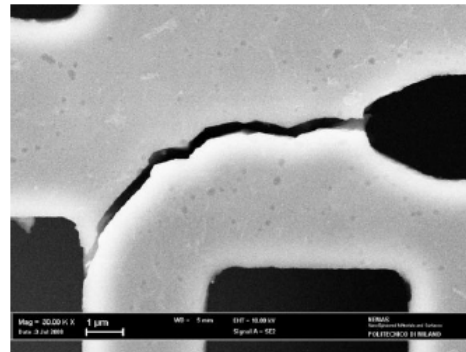
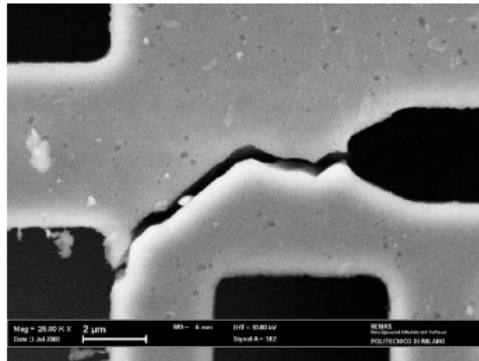
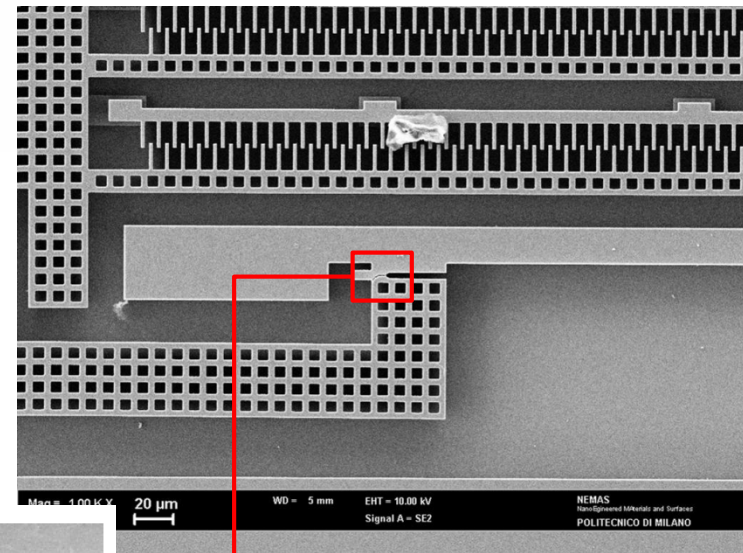
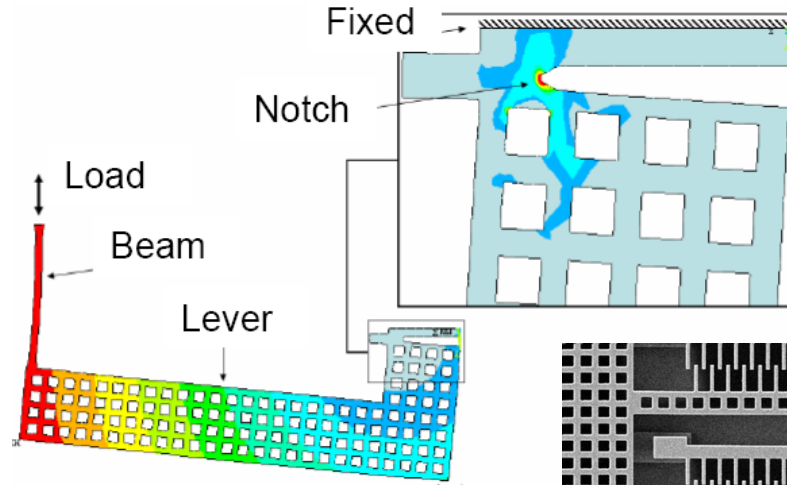


Multi-scale analysis of MEMS subject to mechanical shocks:

- decoupling between macro-scale and meso-scale allowed by small inertia of the sensor
- decoupling between meso-scale and micro-scale? (not allowed if nonlinear effects to be simulated)

	mass (Kg)
Package	$5 \cdot 10^{-4}$
Die	$2.3 \cdot 10^{-6}$
Sensor	$3 \cdot 10^{-9}$



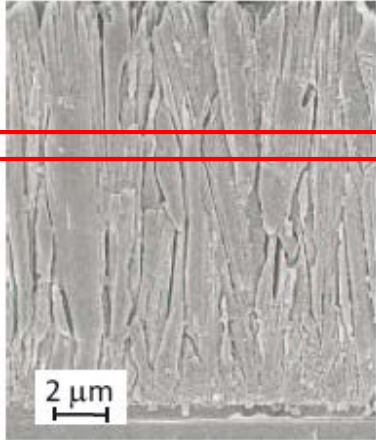


# Meso-scale elastic properties



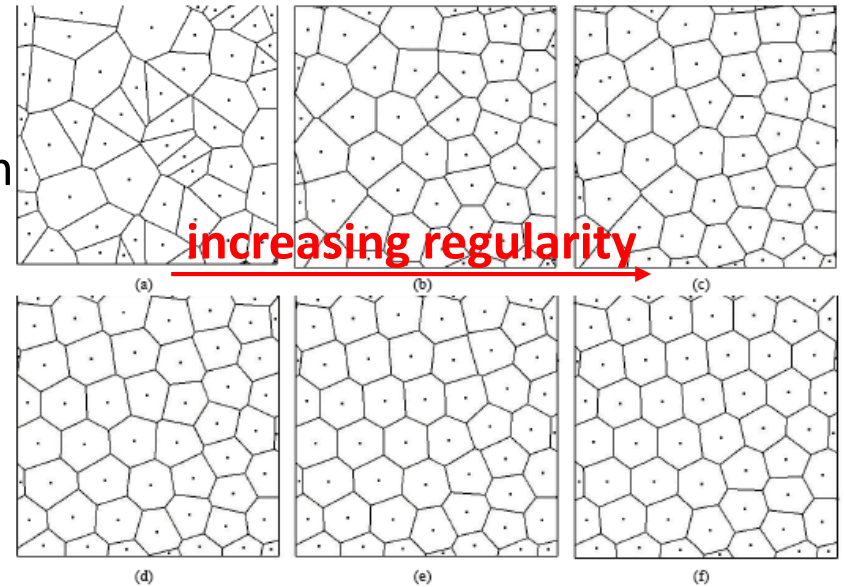
## Homogenization approach

Columnar polysilicon film  
(lateral view)



taking a slice of the film  
(plane stress cond.)

regularized Voronoi tessellations



Through homogenization: in-plane macro strain and stress components (vectors)

$$\mathbf{E} = \{E_{11} \ E_{22} \ E_{12}\}^T$$

$$\mathbf{\Sigma} = \{\Sigma_{11} \ \Sigma_{22} \ \Sigma_{12}\}^T$$

defined as volume averages, according to:

$$\mathbf{\Sigma} = \frac{1}{V} \int_V \boldsymbol{\sigma} dV$$

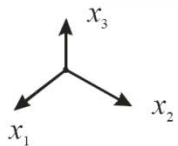
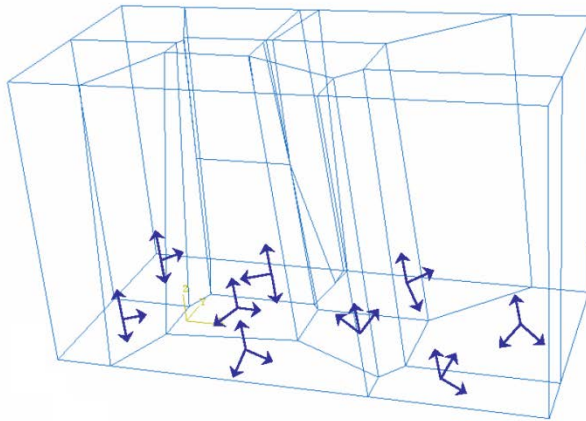
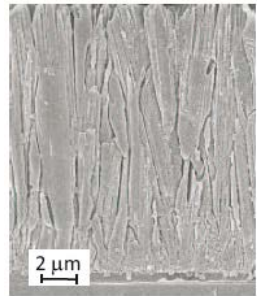
local elastic law

$$\boldsymbol{\sigma} = \mathbf{C}\boldsymbol{\varepsilon}$$

$$\mathbf{E} = \frac{1}{V} \int_V \boldsymbol{\varepsilon} dV$$

Polysilicon assumed to feature:

- one axis of elastic symmetry aligned with epitaxial growth direction  $x_3$
- random orientation of other two elastic symmetry directions in the  $x_1$ -  $x_2$  plane



Matrix of elastic moduli for single-crystal Si (FCC symmetry)

$$\mathbf{c} = \begin{bmatrix} 165.7 & 63.9 & 63.9 & 0 & 0 & 0 \\ 63.9 & 165.7 & 63.9 & 0 & 0 & 0 \\ 63.9 & 63.9 & 165.7 & 0 & 0 & 0 \\ 0 & 0 & 0 & 79.6 & 0 & 0 \\ 0 & 0 & 0 & 0 & 79.6 & 0 \\ 0 & 0 & 0 & 0 & 0 & 79.6 \end{bmatrix} \text{ GPa}$$

Elastic moduli in  $\Sigma = CE$  are numerically bounded through:

- uniform strain boundary cond.

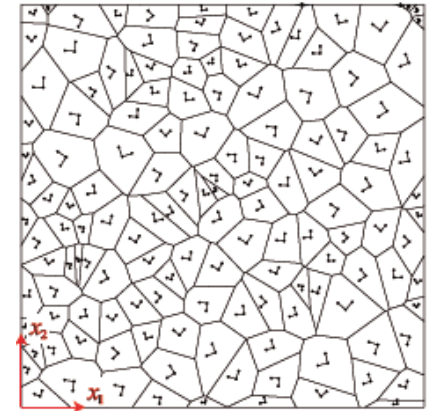
$$u = XE \text{ on } \partial V$$

- uniform stress boundary cond.

$$T = N\Sigma \text{ on } \partial V$$

$$X = \begin{bmatrix} x_1 & 0 & \frac{x_2}{2} \\ 0 & x_2 & \frac{x_1}{2} \end{bmatrix}$$

$$N = \begin{bmatrix} n_1 & 0 & n_2 \\ 0 & n_2 & n_1 \end{bmatrix}$$



**Voigt** and **Reuss** bounds:

from Hill-Mandel macro-homogeneity condition  $\Sigma^T E = \frac{1}{V} \int_V \sigma^T \varepsilon dV = \frac{1}{V} \int_V \sigma_l^T \varepsilon_l dV$

Voigt assumption:  $\varepsilon = E$  everywhere

$$E^T C E = \frac{1}{V} \int_V \varepsilon_l^T c_l \varepsilon_l dV = \frac{1}{V} \int_V \varepsilon^T t_\varepsilon^T c_l t_\varepsilon \varepsilon dV = E^T \left[ \frac{1}{V} \int_V t_\varepsilon^T c_l t_\varepsilon dV \right] E = E^T \left[ \frac{1}{V} \int_V c dV \right] E$$

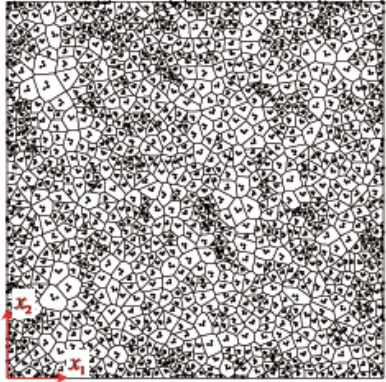
➡  $C = \frac{1}{V} \int_V t_\varepsilon^T c_l t_\varepsilon dV$

Reuss assumption:  $\sigma = \Sigma$  everywhere

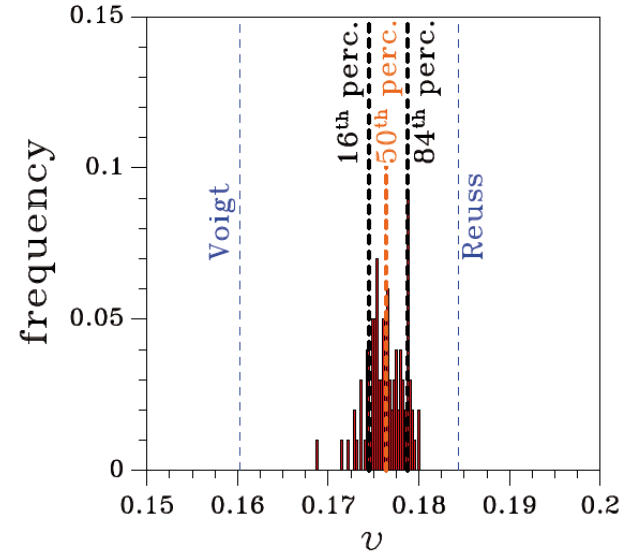
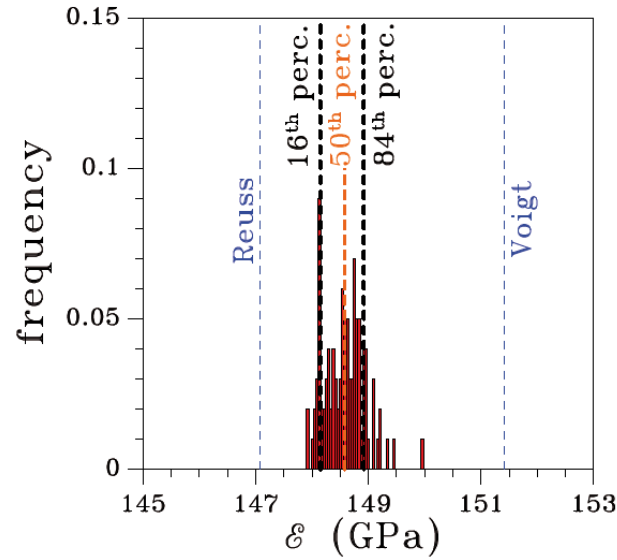
➡  $C^{-1} = \frac{1}{V} \int_V t_\sigma^T c_l^{-1} t_\sigma dV$



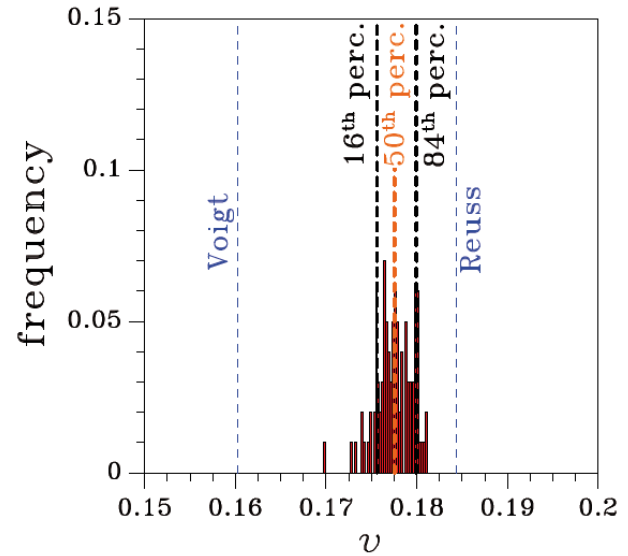
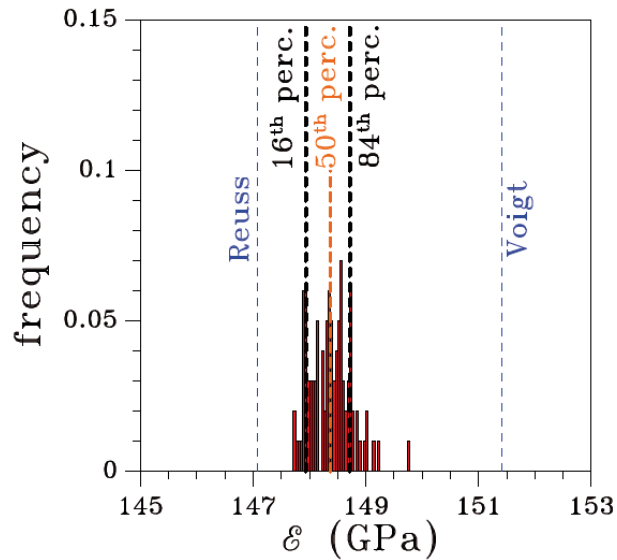
$L = 12 \mu\text{m}$ ,  
 $\bar{s}_g = 0.2 \mu\text{m}$

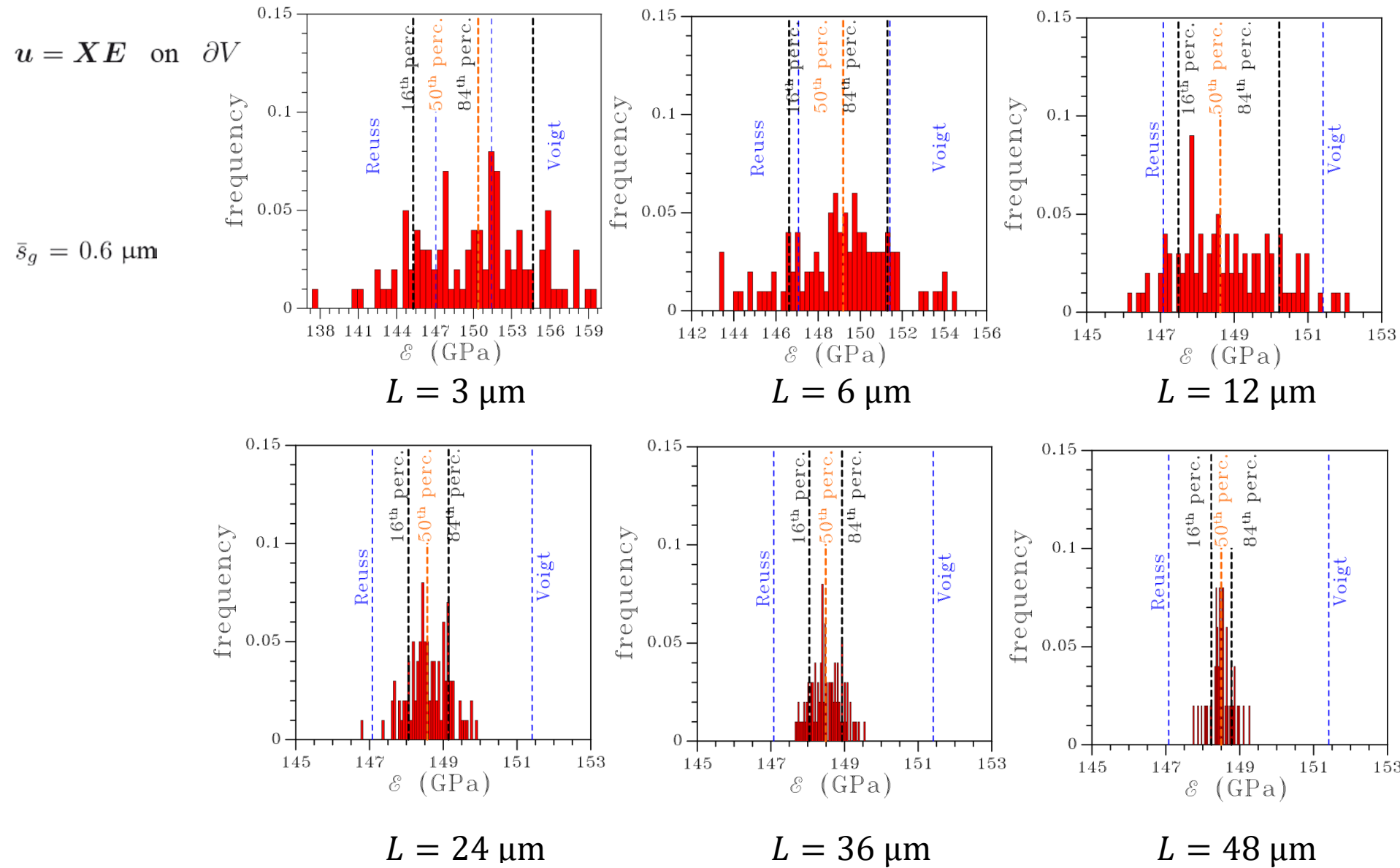


$u = XE$  on  $\partial V$



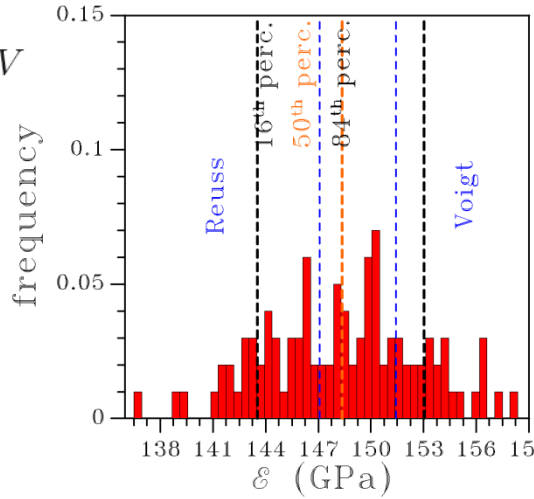
$T = N\Sigma$  on  $\partial V$



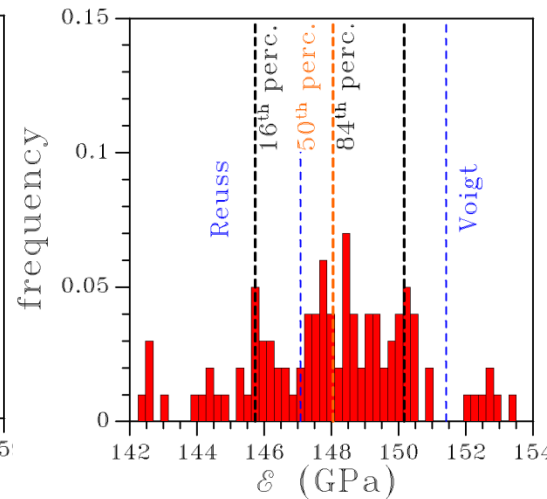


$$T = N\Sigma \text{ on } \partial V$$

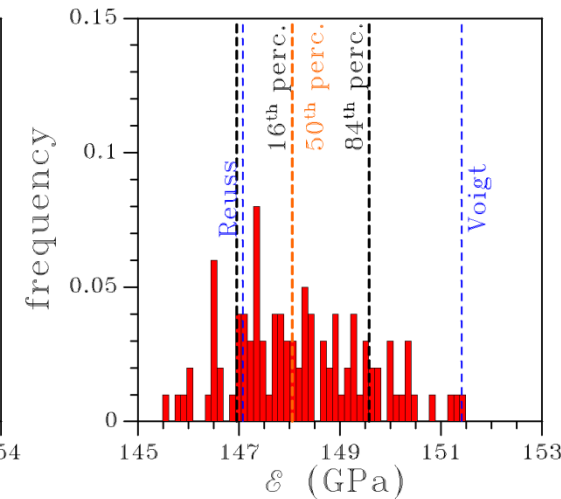
$$\bar{s}_g = 0.6 \mu\text{m}$$



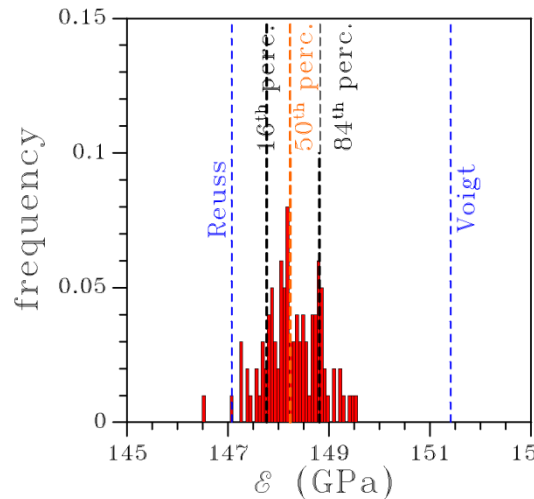
$L = 3 \mu\text{m}$



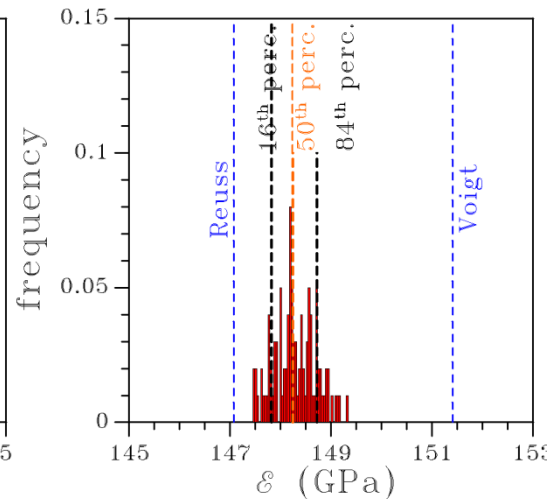
$L = 6 \mu\text{m}$



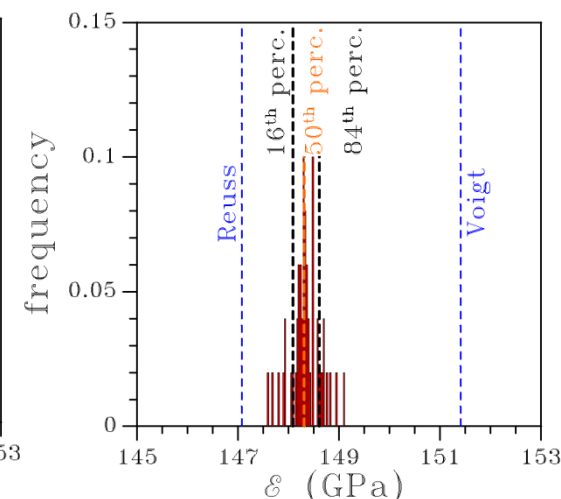
$L = 12 \mu\text{m}$



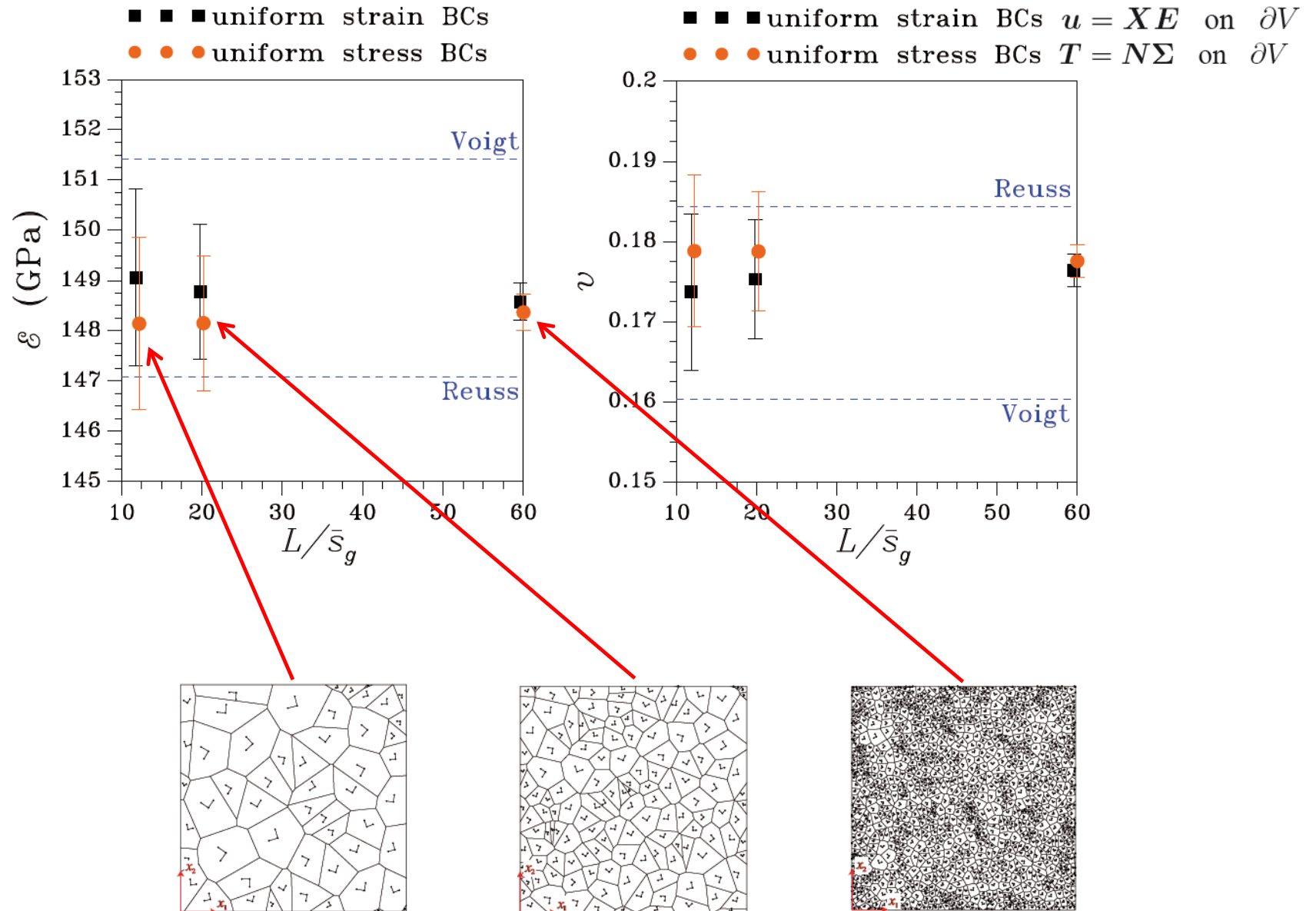
$L = 24 \mu\text{m}$



$L = 36 \mu\text{m}$



$L = 48 \mu\text{m}$



## Deep Learning approach

### INPUT DATA

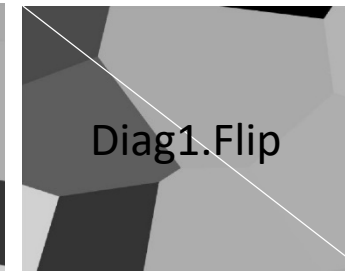
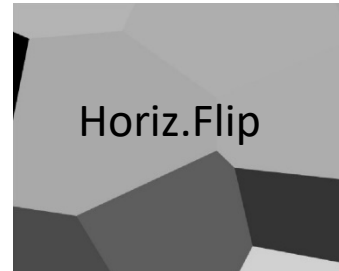
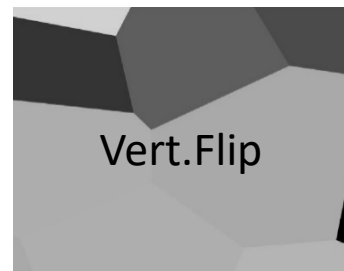
Images resolution= 256x256



Color scale indicate rotations 0°- 45°

192 SVE images+ data augmentation > 1536 images  
(1152 images for training and 384 images for validation)

Data augmentation



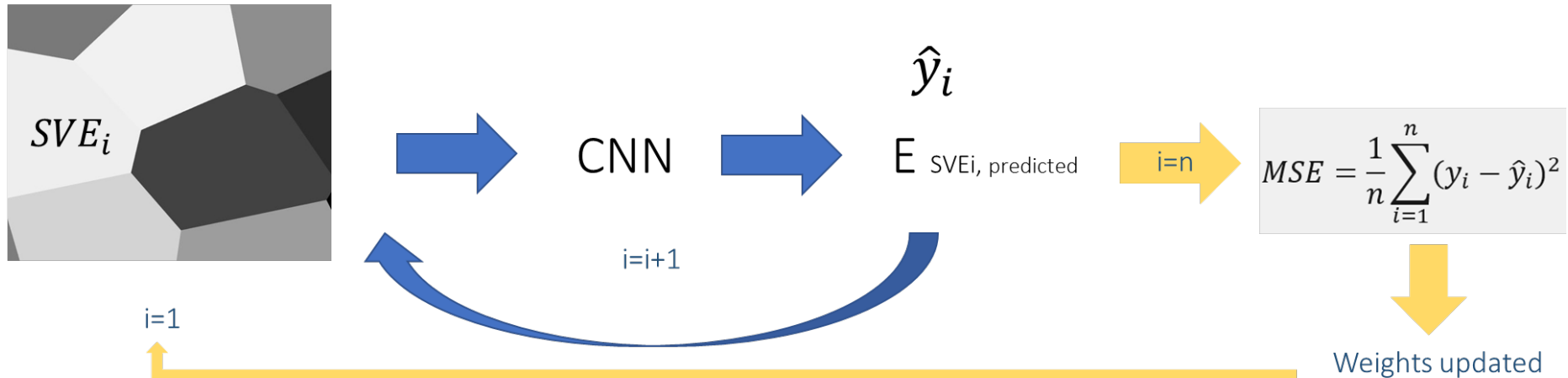


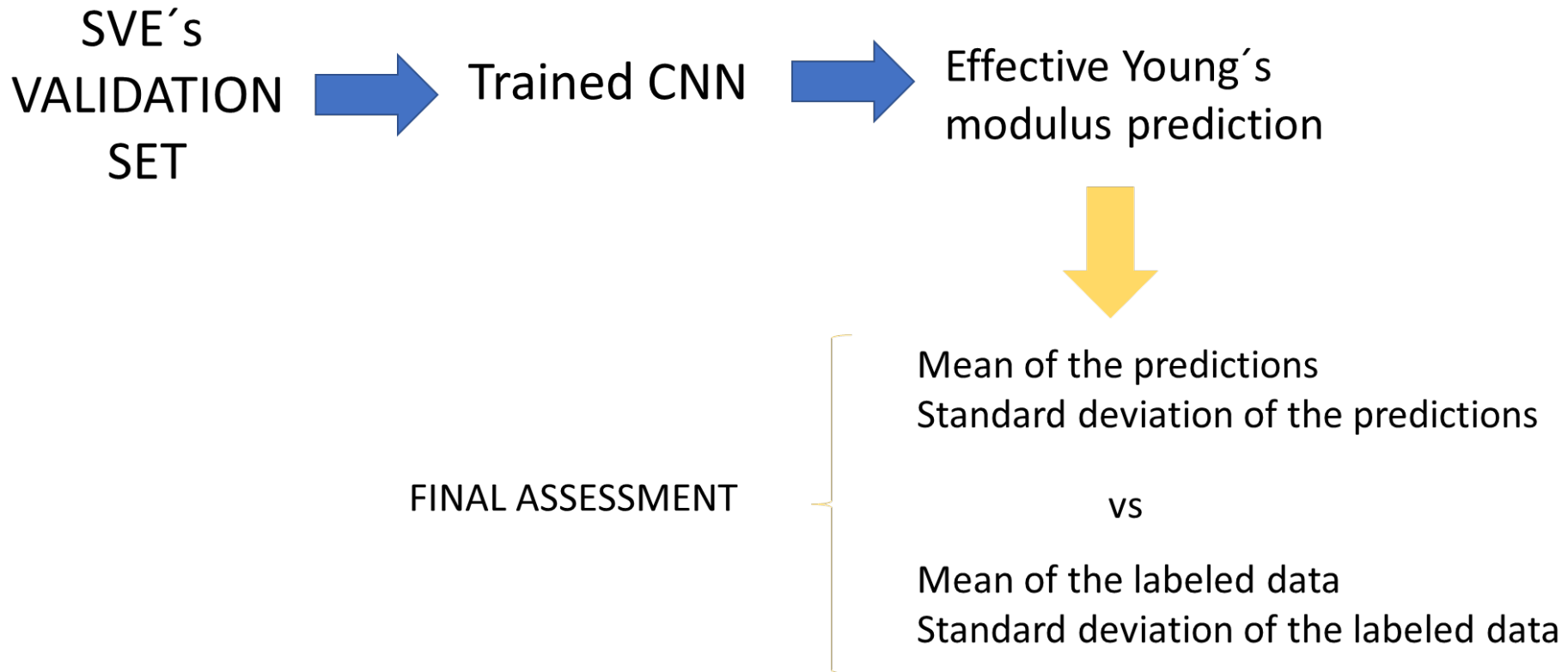
## SOME RELEVANT HYPERPARAMETERS

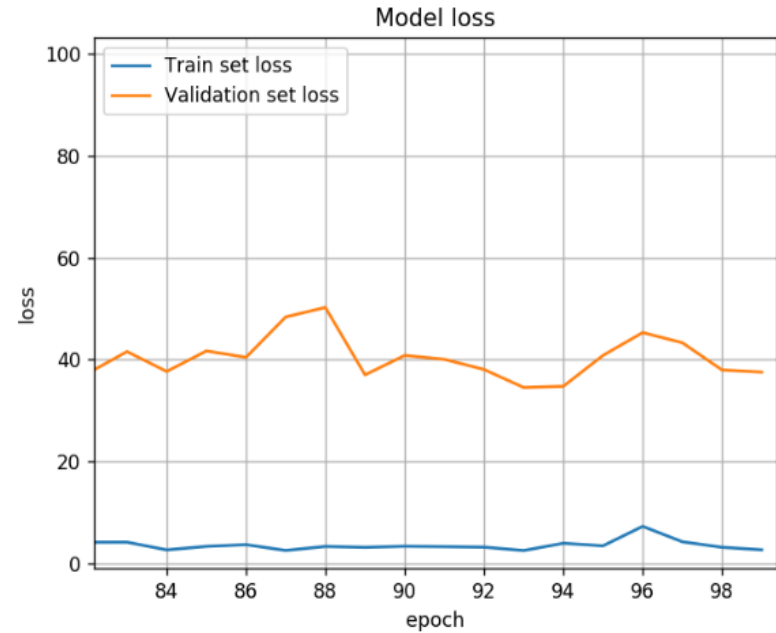
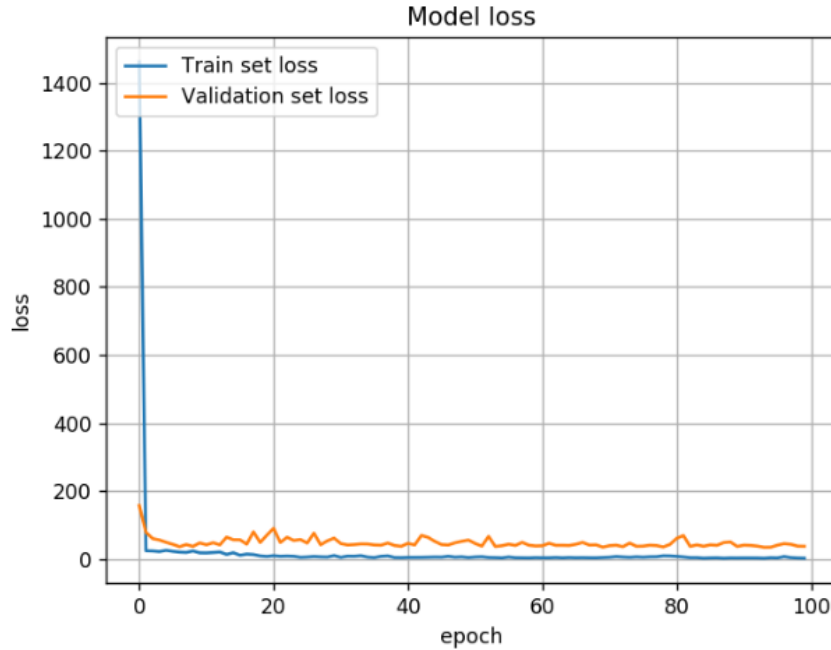
- Optimizer=Adam(lr=5e-4, decay=5e-4/200)
- Loss Function=Mean Squared Error
- Training epochs=100
- Batch size = 32

## TRAINING PROCEDURE

Scheme for 1 epoch

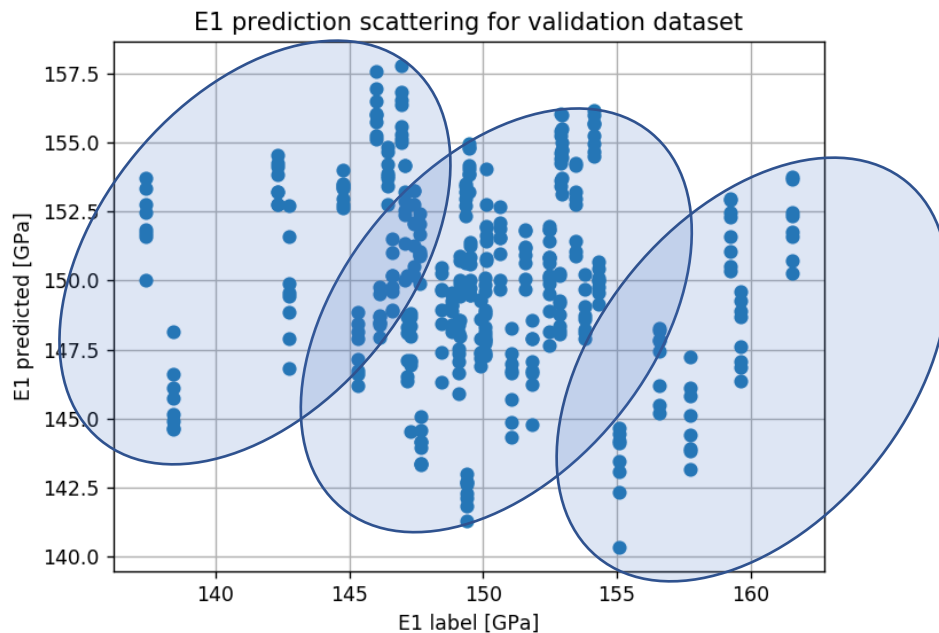






Final training loss = 2.6787 GPa<sup>2</sup>

Final validation loss = 37.5667 GPa<sup>2</sup>



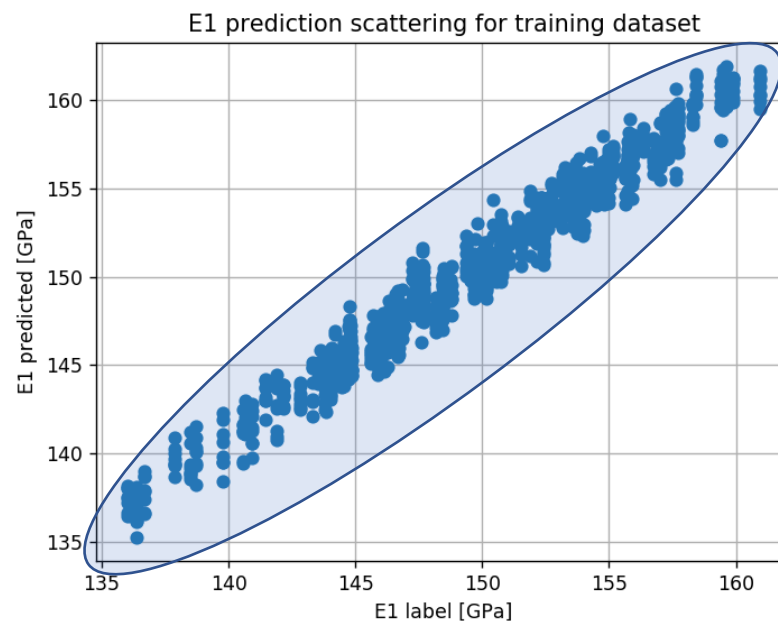
$E_m = 150.0$  GPa,  $E_s = 3.4$  GPa for the validation set

vs

$E_m = 149.9$  GPa,  $E_s = 4.8$  GPa  
for the validation set labels

0,067% absolute error in E1 Mean

29,16% absolute error in E1 Standard Deviation



$E_m = 150.5$  GPa,  $E_s = 5.5$  GPa for the training set.

vs

$E_m = 149.7$  GPa,  $E_s = 5.5$  GPa  
for the labeled training set labels

0,53% absolute error in E1 Mean

0% absolute error in E1 Standard Deviation